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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
LP	6,459,118 B1	10/02	Kang			
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LP	K. Noda et al., "A Boosted Dual Word-line Decoding Scheme for 256Mb DRAMs" Symposium on VLSI Circuits Digest of Technical Papers; pp. 112-113; 1992.
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EXAMINER	DATE CONSIDERED
	06/23/2004

EXAMINER: Initial citation if reference was considered. Draw line through citation if not in conformance to MPEP 609 and not considered. Include copy of this form with next communication to applicant.